

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C
60V	16mΩ @ V _{GS} = 10V	31A
	24mΩ @ V _{GS} = 4.5V	24A

Description

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize R_{DS(ON)} and yet maintain superior switching performance. This device is ideal for use in Notebook battery power management and load switch.

Applications

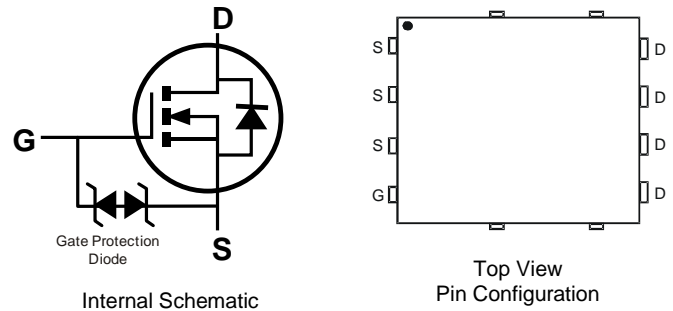
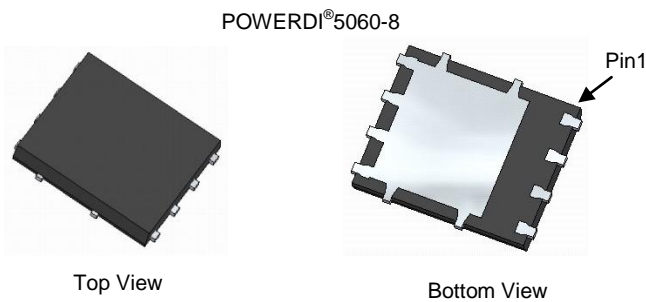
- Motor Control
- DC-DC Converters
- Power Management

Features

- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low R_{DS(ON)} – Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile – Ideal for Thin Applications
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**

Mechanical Data

- Case: POWERDI®5060-8
- Case Material: Molded Plastic, “Green” Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe;
Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)

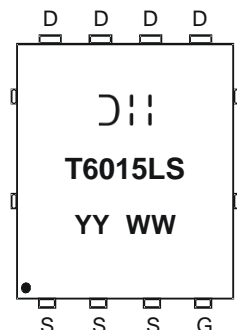


Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6015LPS-13	POWERDI®5060-8	2,500 / Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



DII = Manufacturer's Marking
 T6015LS = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 14 = 2014)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	60	V
Gate-Source Voltage	V _{GSS}	±16	V
Continuous Drain Current (Note 6) V _{GS} = 10V	T _A = +25°C	10.6	A
	T _A = +70°C	8.5	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	T _C = +25°C	31	A
	T _C = +70°C	25	A
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	2	A
Avalanche Current (Note 7) L=0.1mH	I _{AS}	10	A
Avalanche Energy (Note 7) L=0.1mH	E _{AS}	5	mJ
V _{DS} Spike	t=10μs V _{SPIKE}	75	V

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	1.16	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	108	°C/W
	t<10s	56	
Total Power Dissipation (Note 6)	P _D	2.7	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	46	°C/W
	t<10s	24	
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	4.4	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 48V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±16V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	0.5	—	2.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	14.2	16	mΩ	V _{GS} = 10V, I _D = 10A
		—	18	24		V _{GS} = 4.5V, I _D = 6A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{ISS}	—	1103	—	pF	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{OSS}	—	251.3	—		
Reverse Transfer Capacitance	C _{RSS}	—	19.7	—		
Gate Resistance	R _G	—	1.5	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	8.9	—	nC	V _{DS} = 30V, I _D = 10A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	18.9	—		
Gate-Source Charge	Q _{gs}	—	3.0	—		
Gate-Drain Charge	Q _{gd}	—	2.8	—		
Turn-On Delay Time	t _{D(ON)}	—	4.1	—	ns	V _{GS} = 10V, V _{DS} = 30V, R _G = 6Ω, I _D = 10A
Turn-On Rise Time	t _R	—	7.1	—		
Turn-Off Delay Time	t _{D(OFF)}	—	19.5	—		
Turn-Off Fall Time	t _F	—	8.6	—		
Reverse Recovery Time	t _{RR}	—	21.2	—	ns	I _F = 10A, di/dt = 100A/μs
Reverse Recovery Charge	Q _{RR}	—	13.2	—	nC	

- Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1 inch square copper plate.
7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

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DMT6015LPS

Document number: DS37321 Rev. 3 - 2

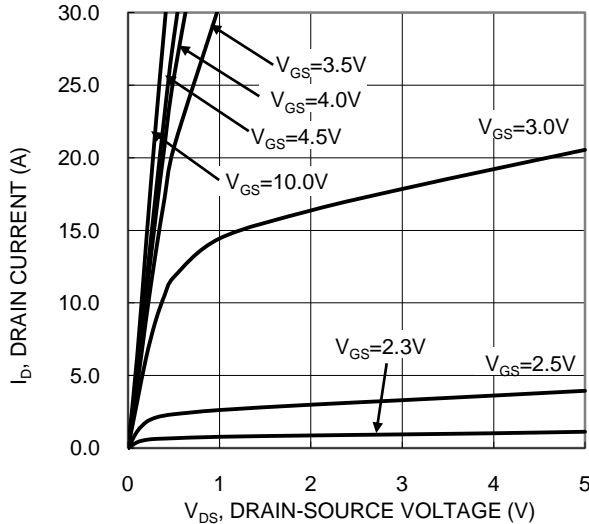


Figure 1. Typical Output Characteristic

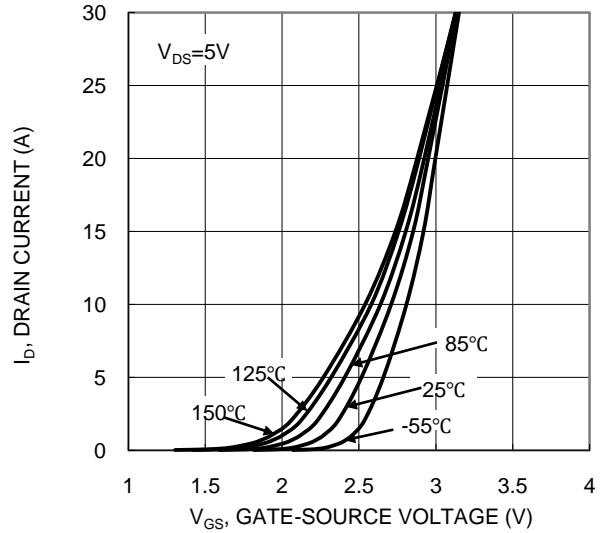


Figure 2. Typical Transfer Characteristic

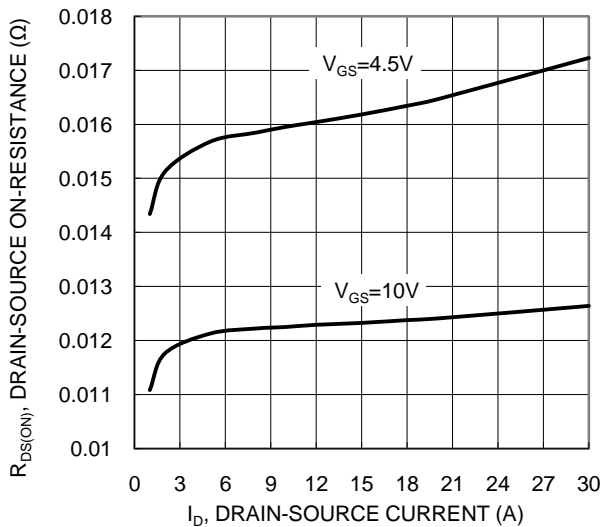


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

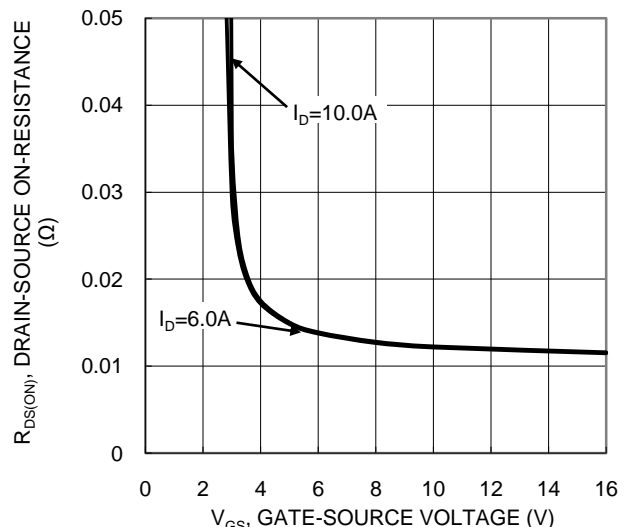


Figure 4. Typical Transfer Characteristic

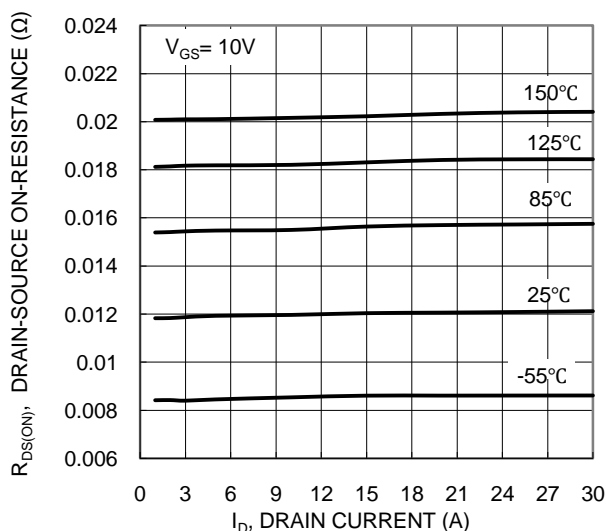


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

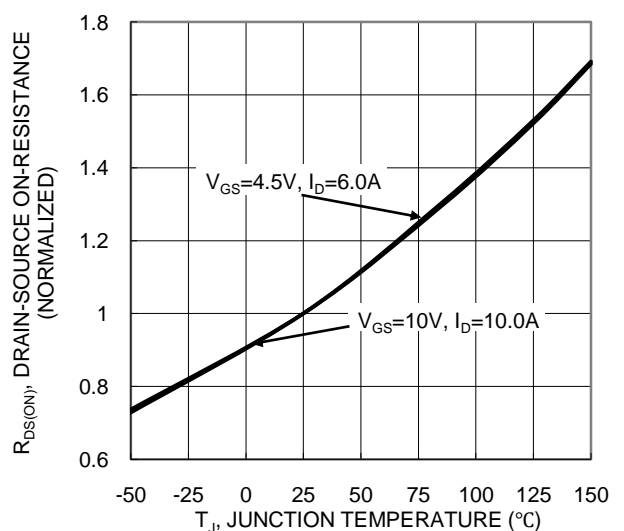


Figure 6. On-Resistance Variation with Temperature

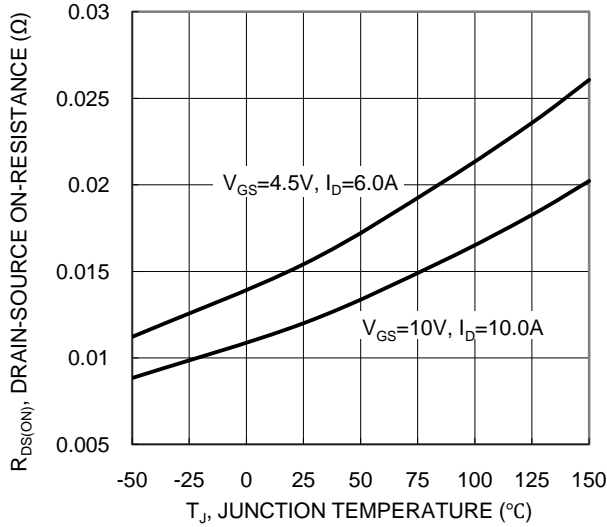


Figure 7. On-Resistance Variation with Temperature

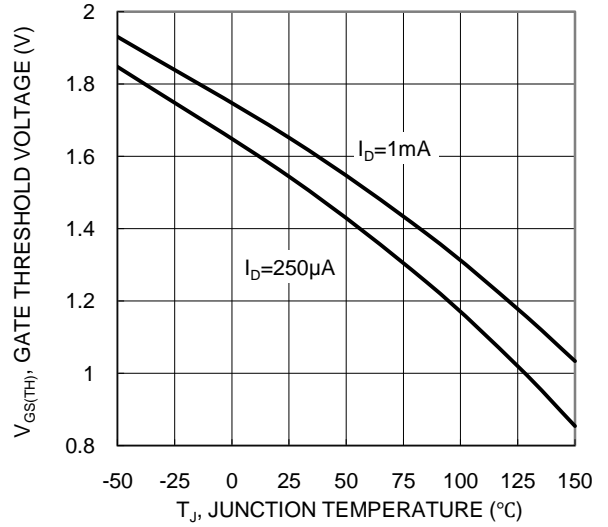


Figure 8. Gate Threshold Variation vs. Temperature

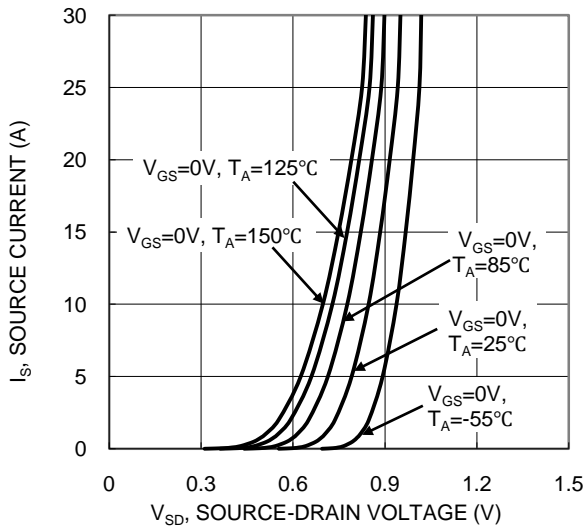


Figure 9. Diode Forward Voltage vs. Current

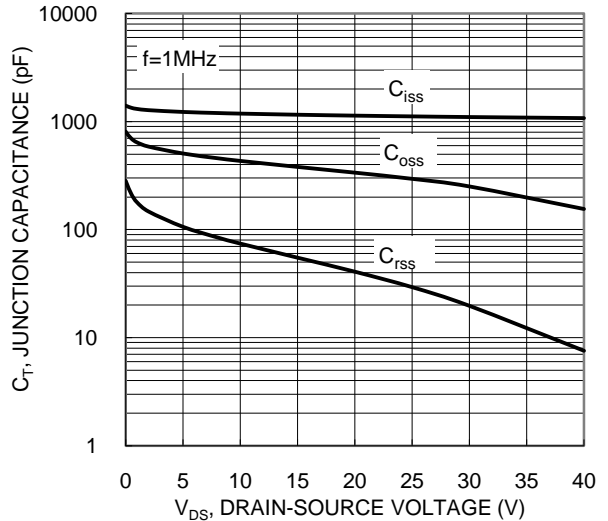


Figure 10. Typical Junction Capacitance

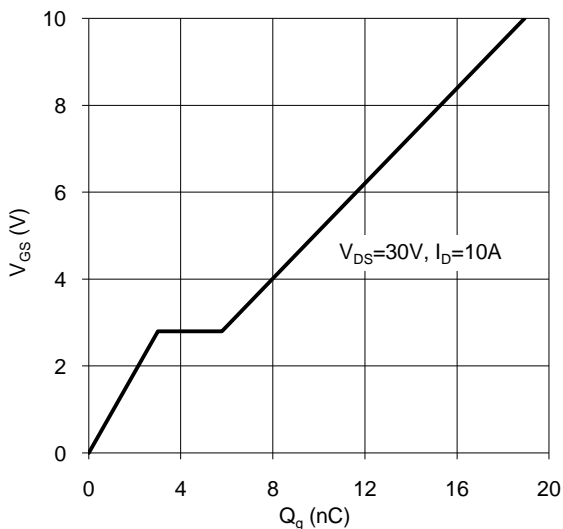


Figure 11. Gate Charge

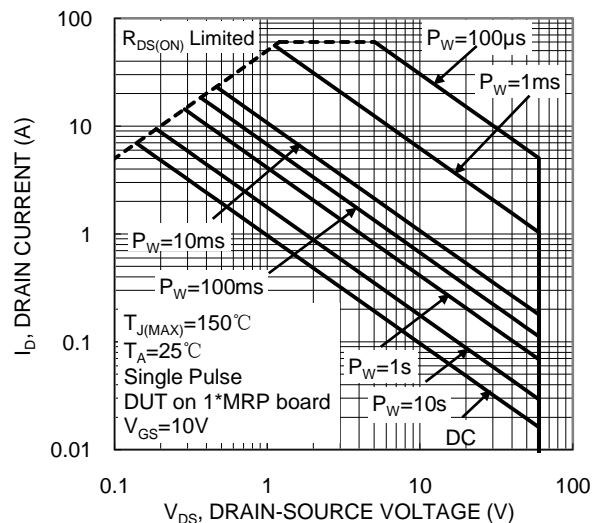


Figure 12. SOA, Safe Operation Area

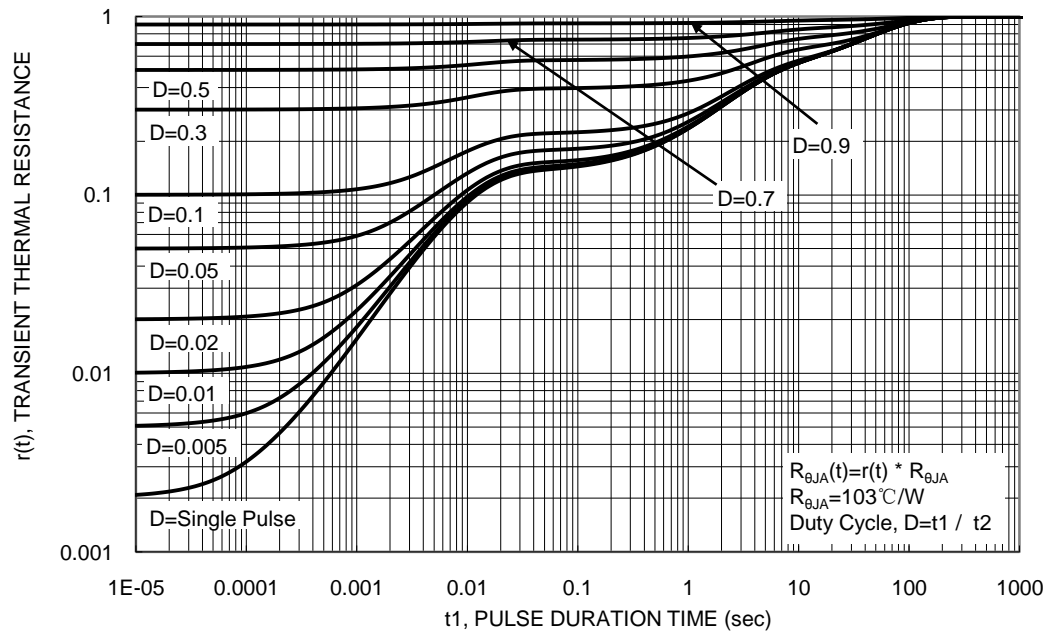
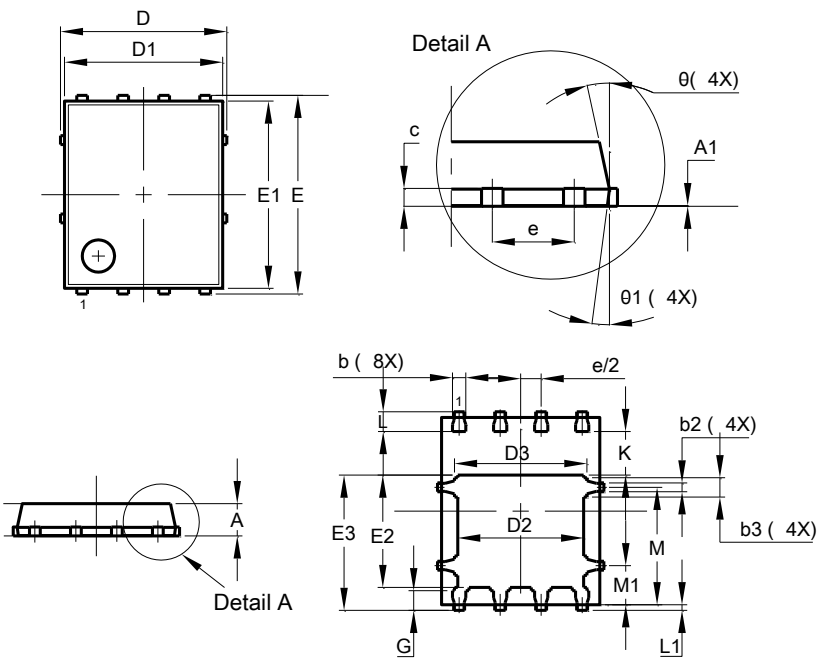


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

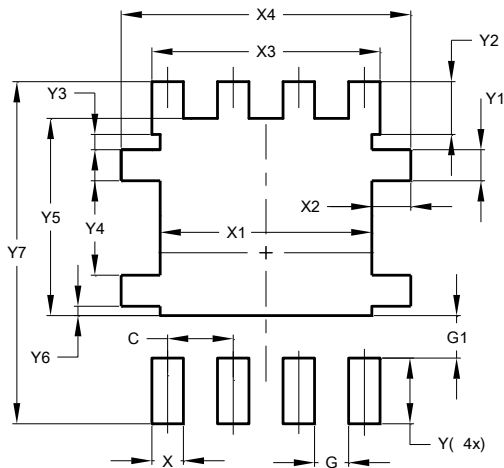
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



POWERDI [®] 5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	-
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	-	-
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
theta	10°	12°	11°
theta1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

NEW PRODUCT

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